SEMICONDUCTOR

DS061N10G

80A 100V N-Channel Enhancement Mode Power MOSFET

Features

- Extremely low on-resistance RDS(on)
- Excellent Qg x RDS(on) product(FOM)
- Rohs compliant

Product Summary			
V_{DS}	$R_{DS(on)}$ (mΩ) Typ	I_D (A)	Qg (Typ)
100V	6. 1 @ 10V 40A	80	67nc

Mechanical Data

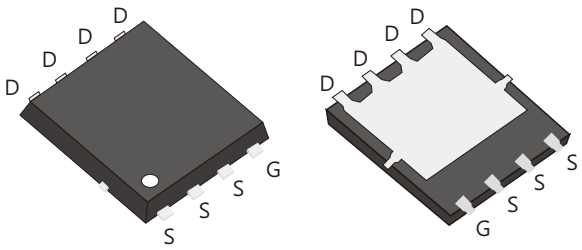
- Case:DFN5×6 Package

DFN5×6

DS061N10G

Application

- Battery management
- UPS (Uninterrupible Power Supplies)
- Synchronous Rectification for AC/DC Quick Charger



Ordering Information

Part No.	Package Type	Package	Quality(box)
DS061N10G	DFN5×6	Tape & Reel	5000

Block Diagram

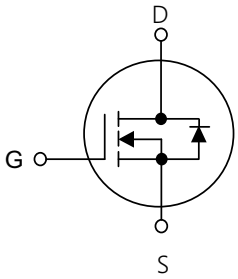


Table1 Absolute Maximum Ratings (T_C=25°C, unless otherwise specified)

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V_{DS}	100	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	T_C=25°C	I_D	80	A
	T_C=100°C		52	
Pulsed Drain Current (Note 1)		I_{DM}	420	A
Single Pulse Avalanche Energy(Note 2)		E_{AS}	330	mJ
Power Dissipation	T_C=25°C	P_D	100	W
Operating Junction and Storage Temperature		T_J/T_{STG}	-55~+150	°C

Table 2.Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal resistance Junction to Ambient	$R_{\theta JA}$	64	°C/W
Thermal resistance Junction to Case	$R_{\theta JC}$	1.25	°C/W

Table 3. Electrical Characteristics (T_J=25°C, unless otherwise specified)

Parameter		Symbol	Test Conditions	Min	Typ	Max	Unit
Off Characteristics							
Drain-Source Breakdown Voltage		BV_{DSS}	V_{GS}=0V,I_D=250μA	100	-	-	V
Drain-Source Leakage Current		I_{DSS}	V_{DS}=100V,V_{GS}=0V	-	-	1	μA
Gate- Source Leakage Current	Forward	I_{GSS}	V_{GS}=20V,V_{DS}=0V	-	-	100	nA
	Reverse		V_{GS}=-20V,V_{DS}=0V	-	-	-100	nA
On Characteristics(Note 3)							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS}=V_{GS},I_D=250μA	1.2	1.7	2.5	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS}=10V,I_D=40A	-	6.1	7.2	mΩ
Dynamic Characteristics(Note 4)							
Input Capacitance		C_{ISS}	V_{DS}=50V,V_{GS}=0V,f=1MHz	-	3931	-	pF
Output Capacitance		C_{OSS}		-	330	-	pF
Reverse Transfer Capacitance		C_{RSS}		-	20	-	pF
Gate Resisitance		R_G	V_{DD}=0V,V_{GS}=0V,f=1MHz	-	2.5	-	Ω
Switching Characteristics (Note 4)							
Turn-On Delay Time		$t_{d(on)}$	V_{DS}=50V, V_{GS}=10V,R_L=2.7Ω,	-	15.3	-	ns
Turn-On Rise Time		t_R		-	90.1	-	ns
Turn-Off Delay Time		td(off)		-	23.6	-	ns
Turn-Off Fall Time		tf		-	52.4	-	ns
Total Gate Charge		Q_G	V_{DS}=50V,I_D=50A, V_{GS}=10V	-	67	-	nC
Gate-Source Charge		Q_{GS}		-	13	-	nC
Gate-Drain Charge		Q_{GD}		-	15	-	nC
Drain-Source Diode Characteristics and Maximum Ratings							
Drain-Source Diode Forward Voltage		V_{SD}	V_{GS}=0V, I_S=20A	-	0.87	1.4	V
Maximum Continuous Drain-Source Diode Forward Current		I_S		-	-	80	A
Reverse Recovery Time		trr	V_{GS}=0V, I_F=20A dI$_F$/dt=100A/μs	-	60	-	ns
Reverse Recovery Charge		Q_{RR}		-	135	-	nC

Notes : 1 Repetitive Rating:Pulse width limited by maximum junction temperature
2 L=0.5mH, R_G=25Ω,Starting T_J=25°C
3 Pulse Test: Pulse width ≤300μS, Duty cycle≤2%
4 Guaranteed by design,not subject to production

Typical Characteristics Diagrams

Figure 1.Output Characteristics

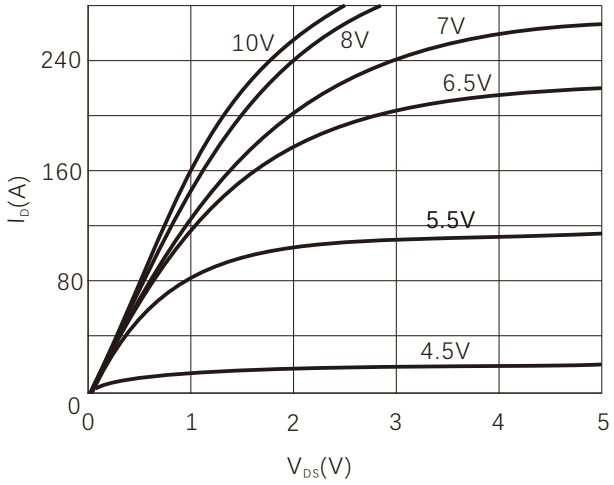


Figure2.Normalized $R_{DS(ON)}$ vs Temperature

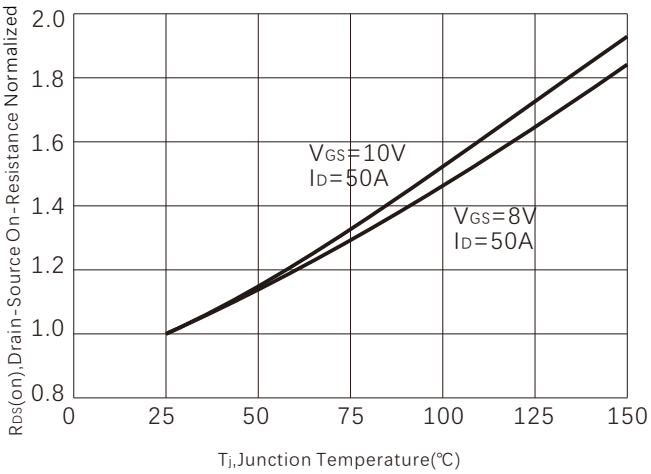


Figure 3.On-Resistance vs.Drain Current

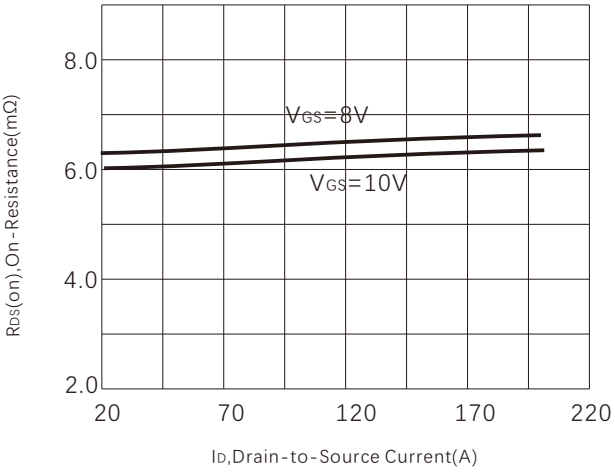


Figure 4. Capacitance

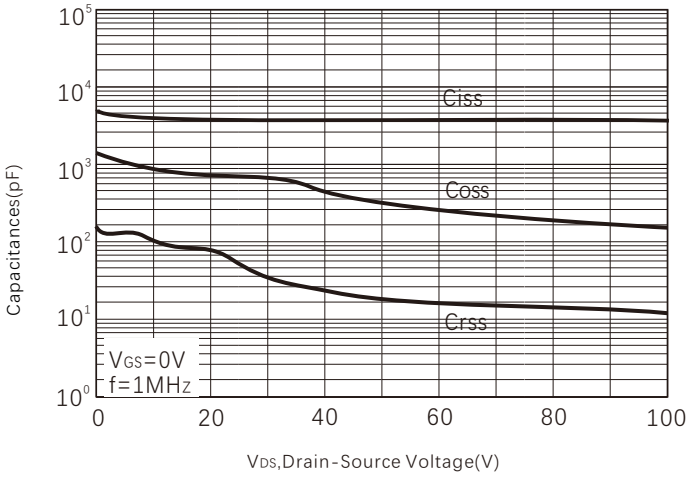


Figure 5.Gate charge

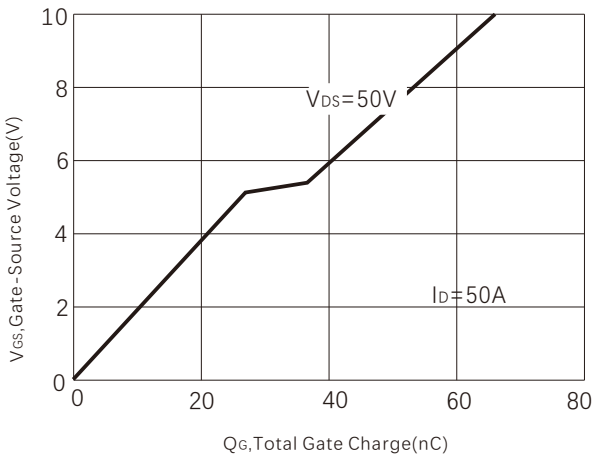


Figure 6.Source-Drain Diode Forward Voltage

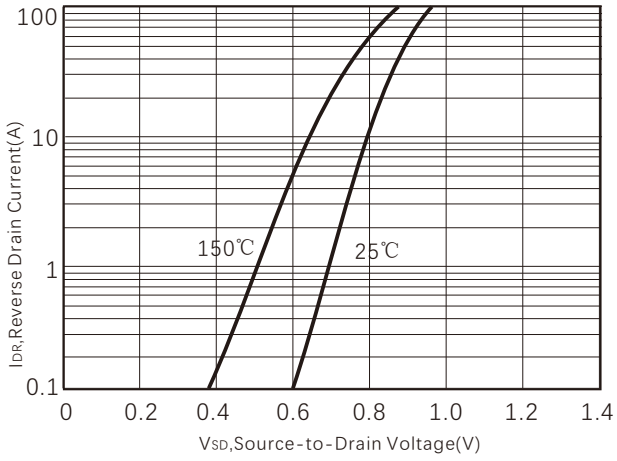


Figure7.Maximum Drain Current vs Temperature

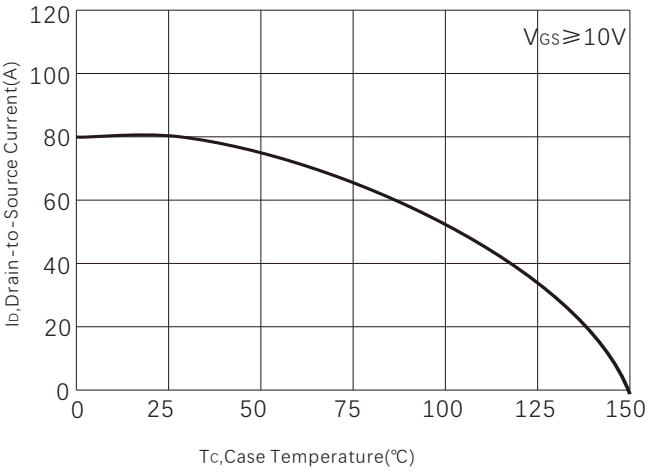


Figure 8. Transfer Characteristics

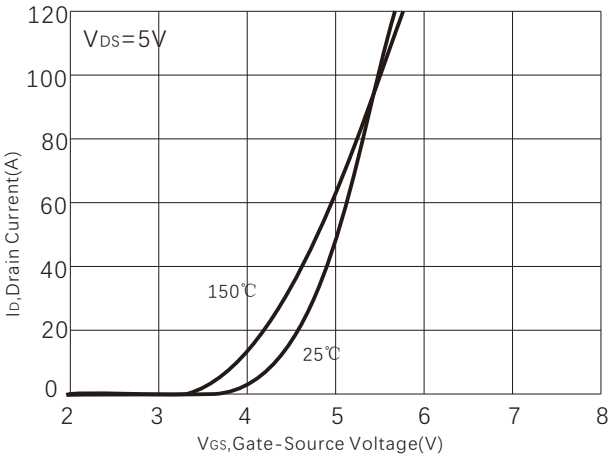


Figure 9. Safe operating area

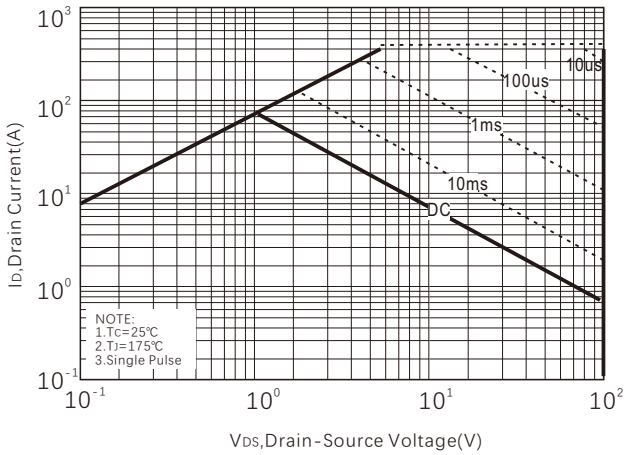
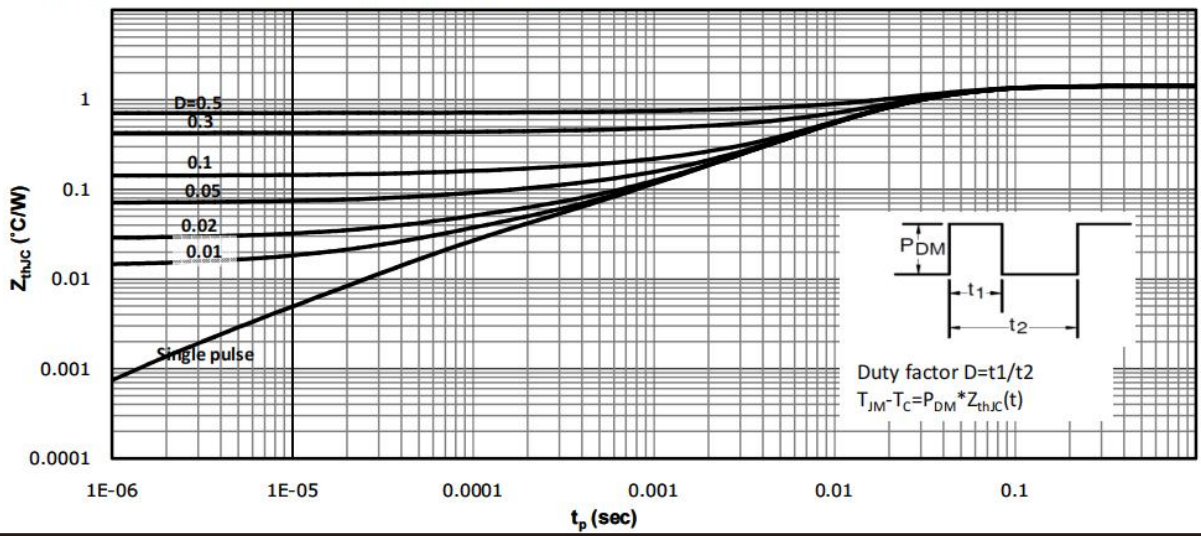
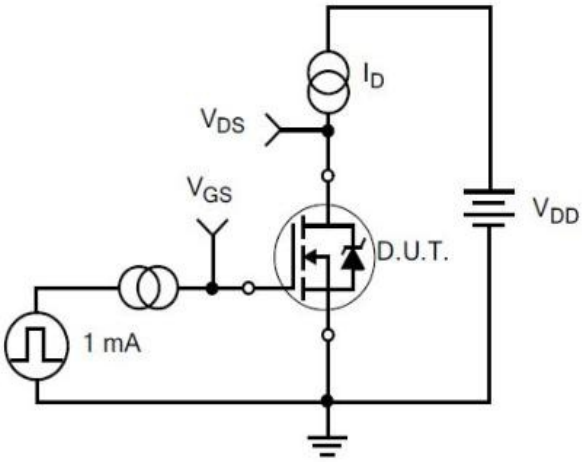


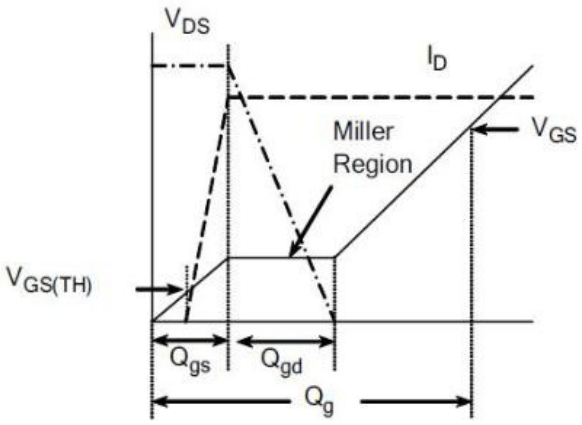
Figure 10. Maximum Transient Thermal Impedance



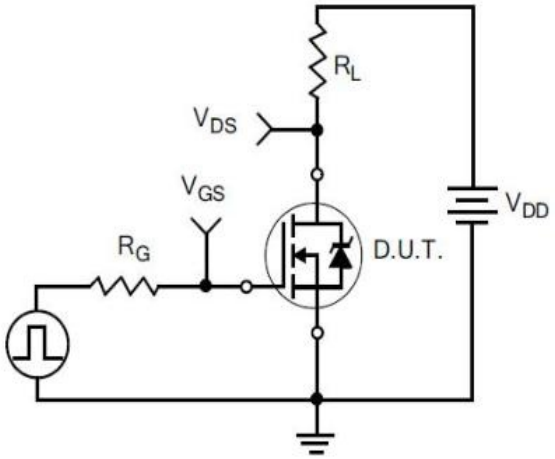
Typical Test Circuit



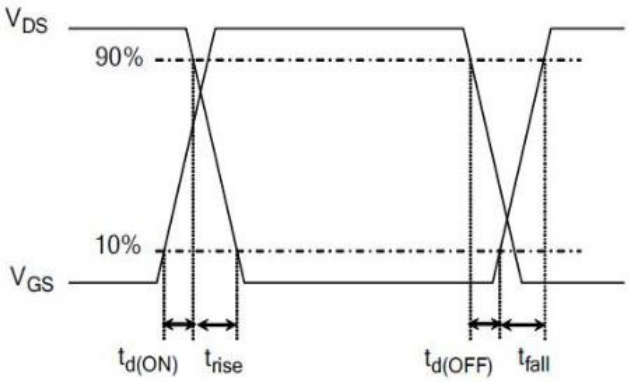
1) Gate Charge Test Circuit



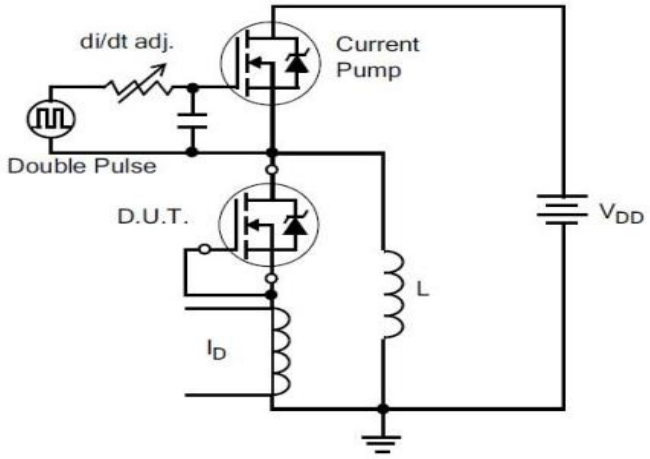
2) . Gate Charge Waveform



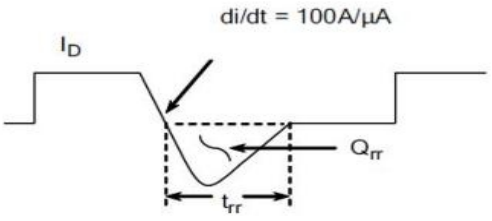
3) Resistive Switching Test Circuit



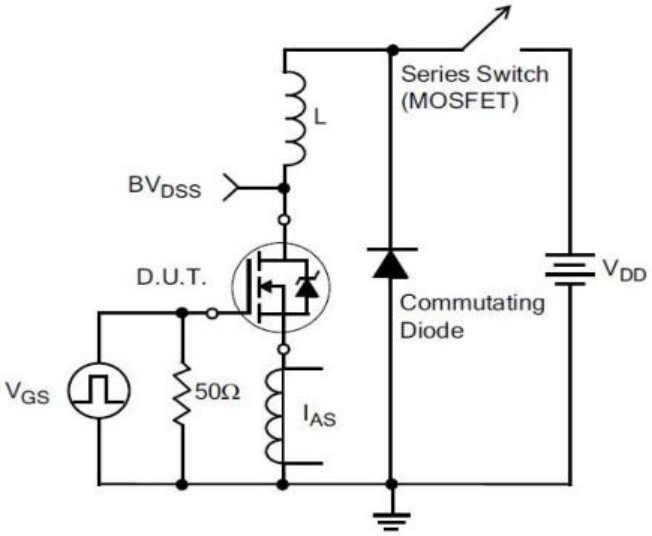
4) Resistive Switching Waveforms



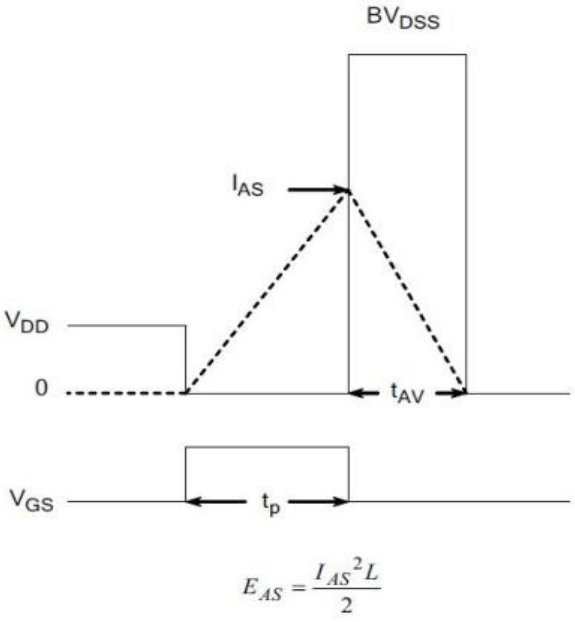
5) Diode Reverse Recovery Test Circuit



6) Diode Reverse Recovery Waveform



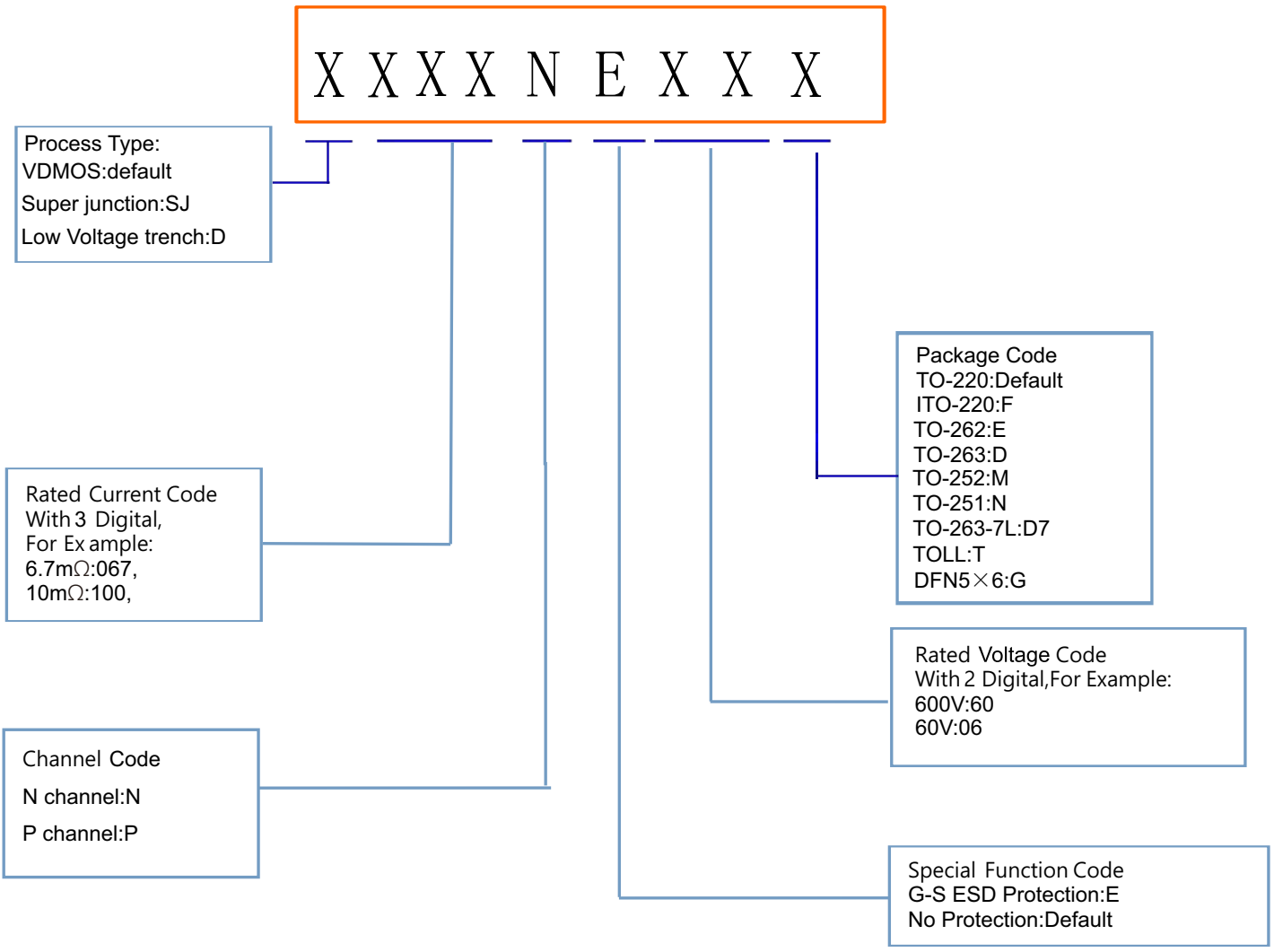
7) . Unclamped Inductive Switching Test Circuit



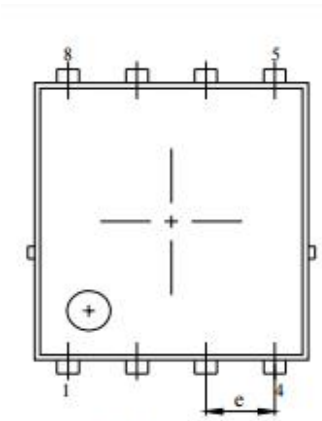
$$E_{AS} = \frac{I_{AS}^2 L}{2}$$

8) Unclamped Inductive Switching Waveforms

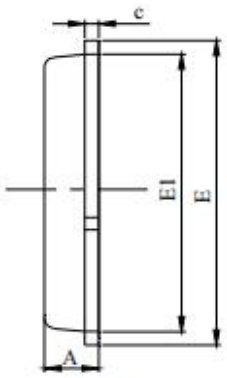
Product Names Rules



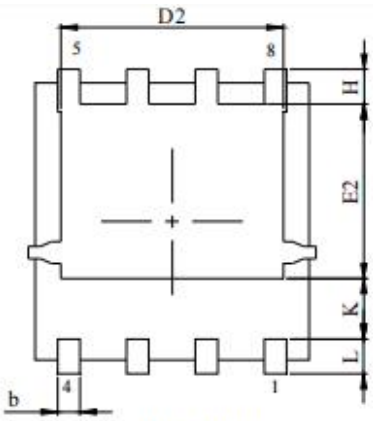
DFN5×6 PACKAGE OUTLINE DIMENSIONS



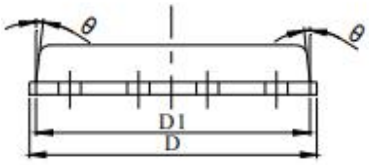
Top View



Side View



Bottom View

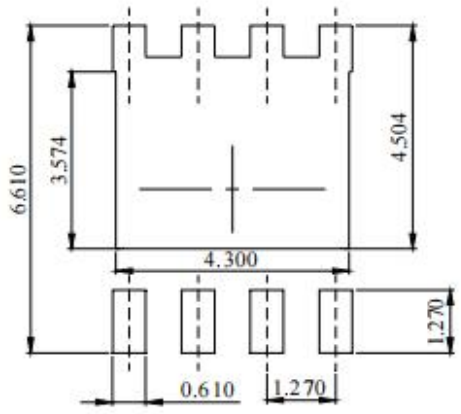


Front View

NOTES:
1. Dimension and tolerance per ASME Y14.5M, 1994.
2. All dimensions in millimeter (angle in degree).
3. Dimensions D1 and E1 do not include mold flash protrusions or gate burrs.

DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
b	0.31	0.41	0.51
c	0.20	0.25	0.30
D	5.00	5.20	5.40
D1	4.95	5.05	5.15
D2	4.00	4.10	4.20
E	6.05	6.15	6.25
E1	5.50	5.60	5.70
E2	3.42	3.53	3.63
e		1.27BSC	
H	0.60	0.70	0.80
L	0.50	0.70	0.80
K		1.23 REF	
θ	-	-	10°

Recommended Soldering Footprint



DIMENSIONS:MILLIMETERS

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